

FIG. 1

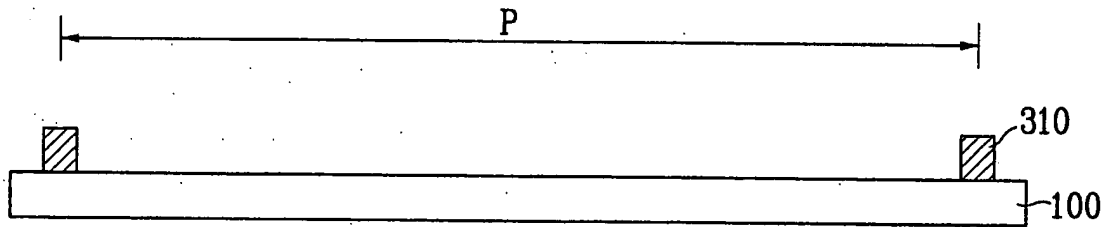


FIG. 2

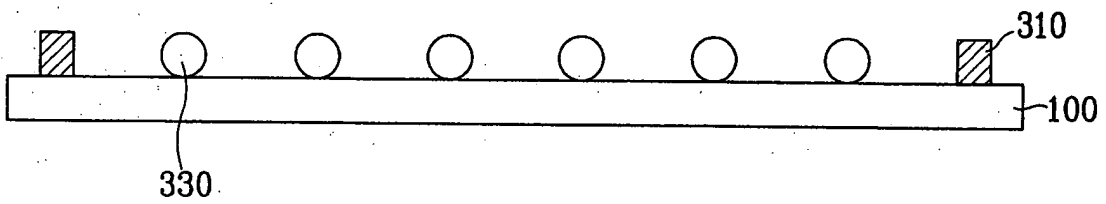


FIG. 3

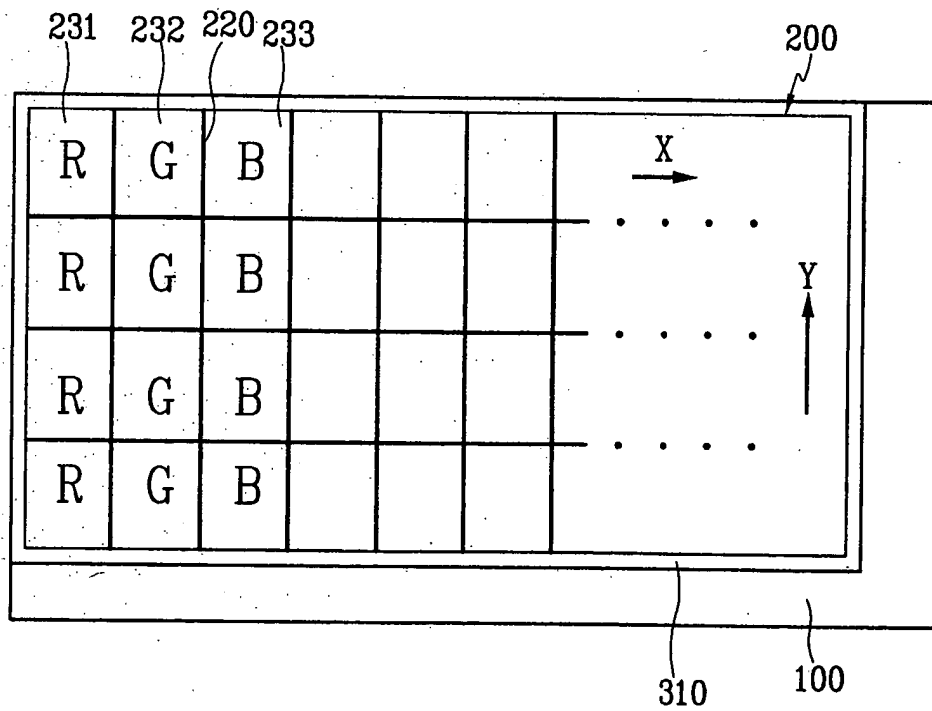


FIG. 4A

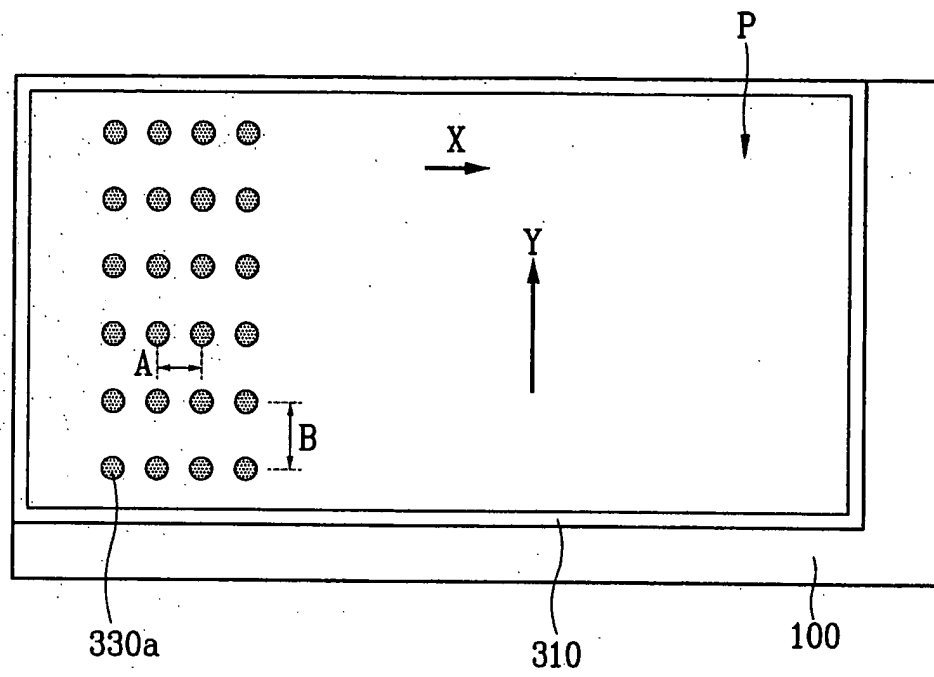


FIG. 4B

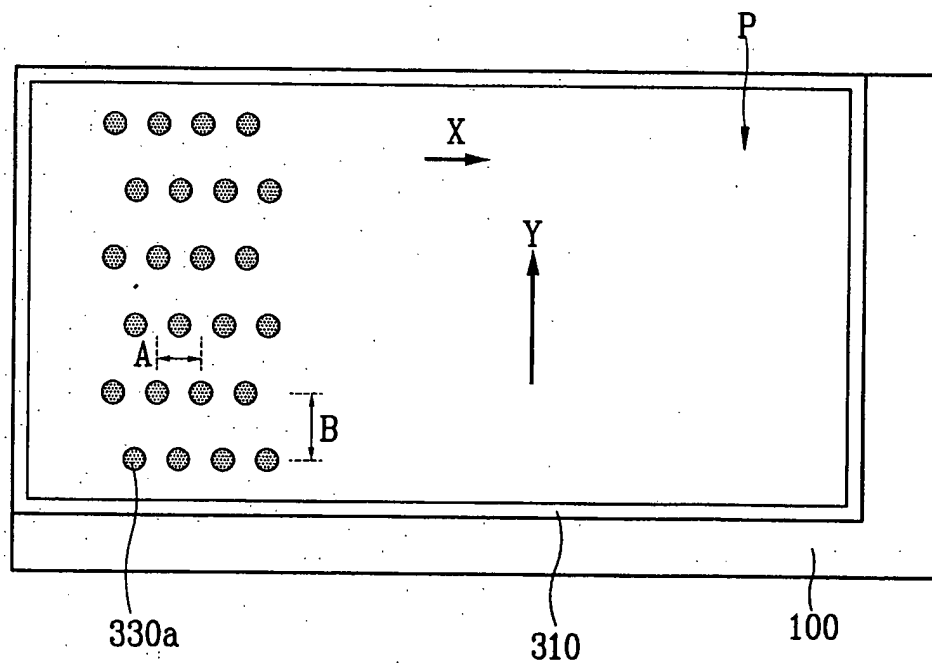


FIG. 5

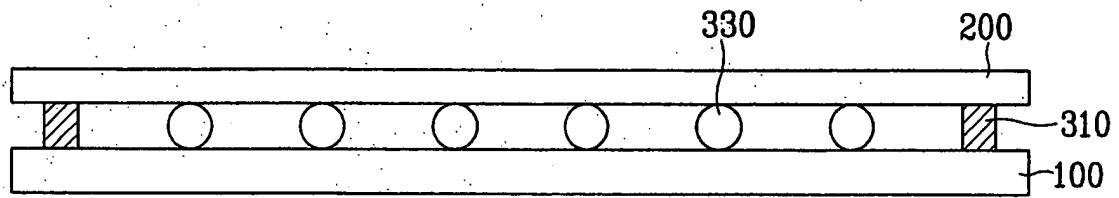


FIG. 6A

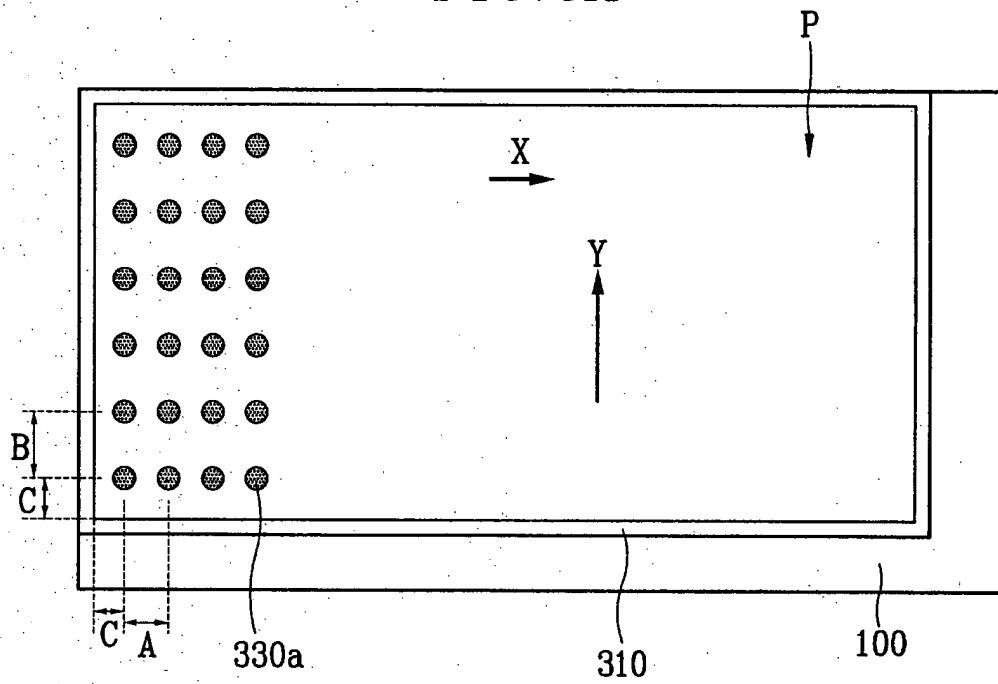


FIG. 6B

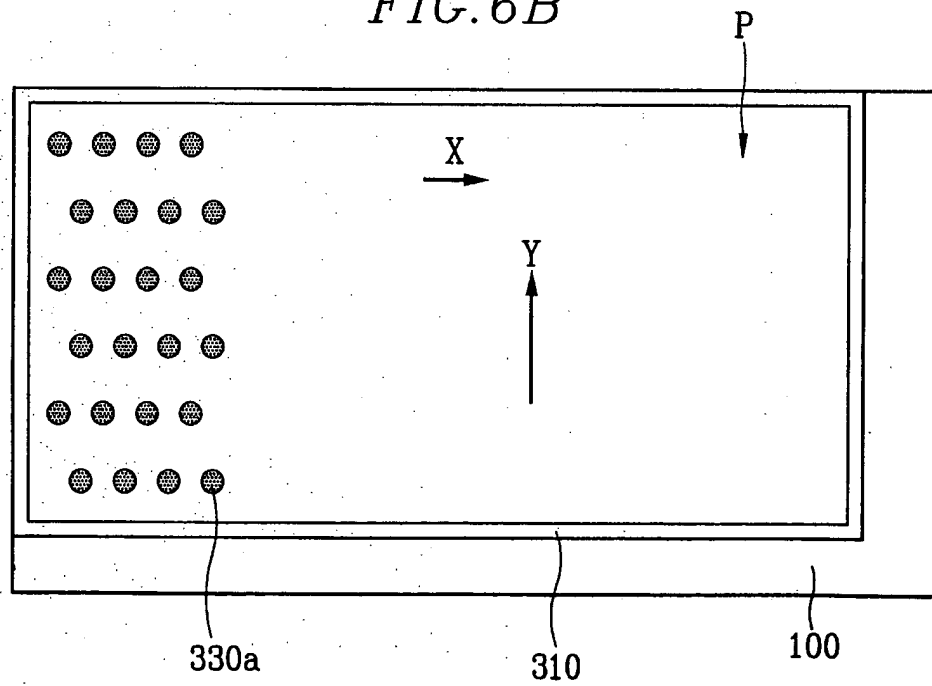


FIG. 7A

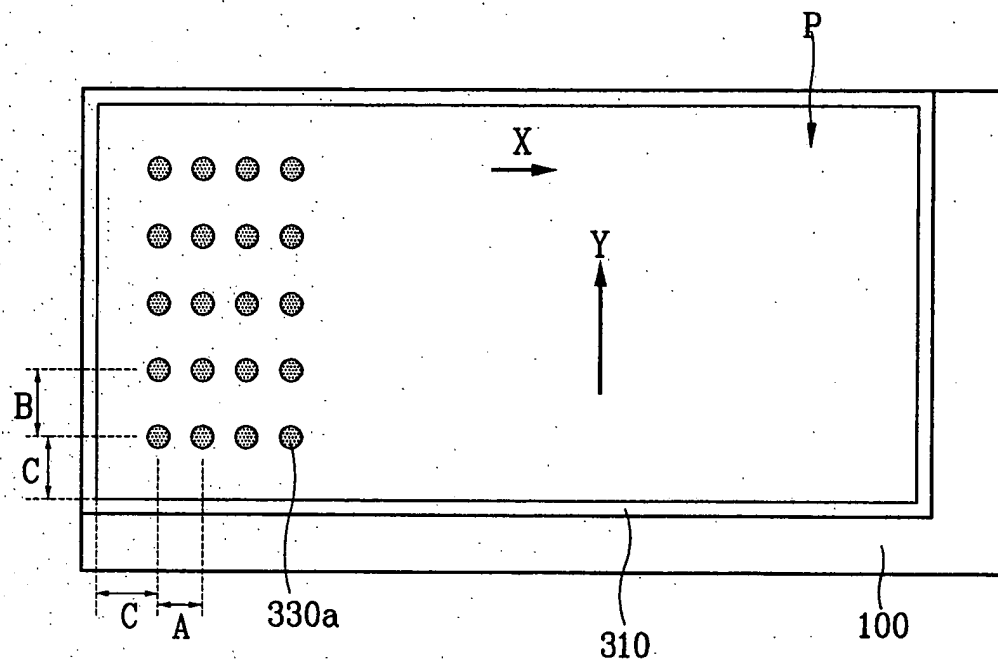
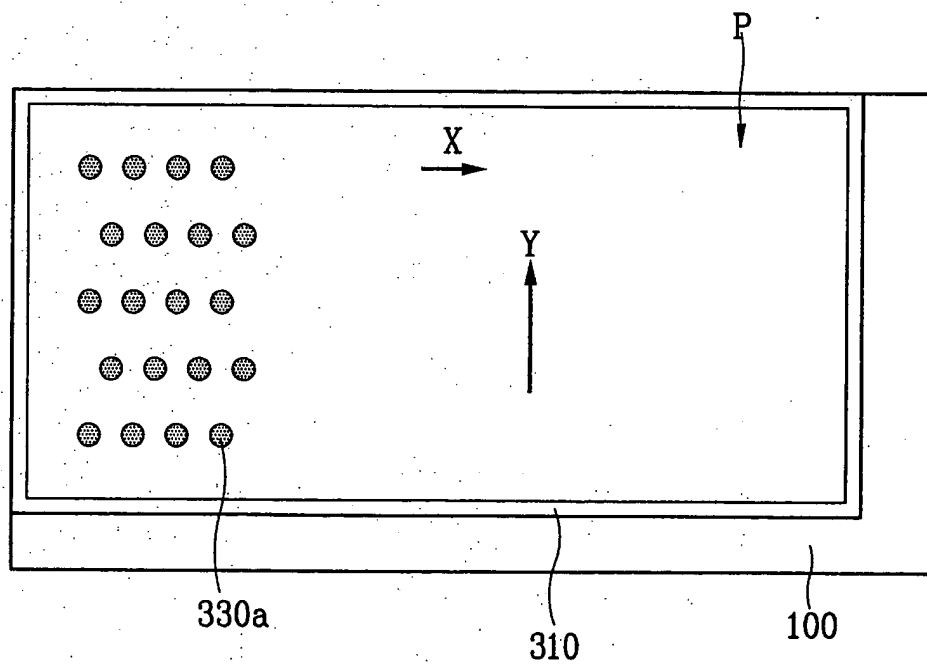


FIG. 7B



Plan view of a substrate 100. A rectangular region 310 is defined within the substrate. In the top-left corner of region 310, there is a grid of circular features 330. The features are arranged in two columns: column 330a (left) and column 330b (right). Column 330a contains 6 features, and column 330b contains 5 features. The horizontal distance between the center of the leftmost feature in column 330a and the center of the leftmost feature in column 330b is dimension A. The vertical distance between the center of the topmost feature in column 330a and the center of the topmost feature in column 330b is dimension B. The vertical distance between the center of the topmost feature in column 330a and the center of the bottommost feature in column 330a is dimension C. A coordinate system is shown with the X-axis pointing right and the Y-axis pointing up. A pressure P is indicated at the top right corner of the substrate 100.

Diagram illustrating a plan view of a semiconductor device 100. The device includes a rectangular region 310. Within this region, there is a grid of circular features, some of which are labeled 330a and 330b. A coordinate system is shown with X and Y axes. A pressure P is indicated by a downward arrow.

FIG. 9A

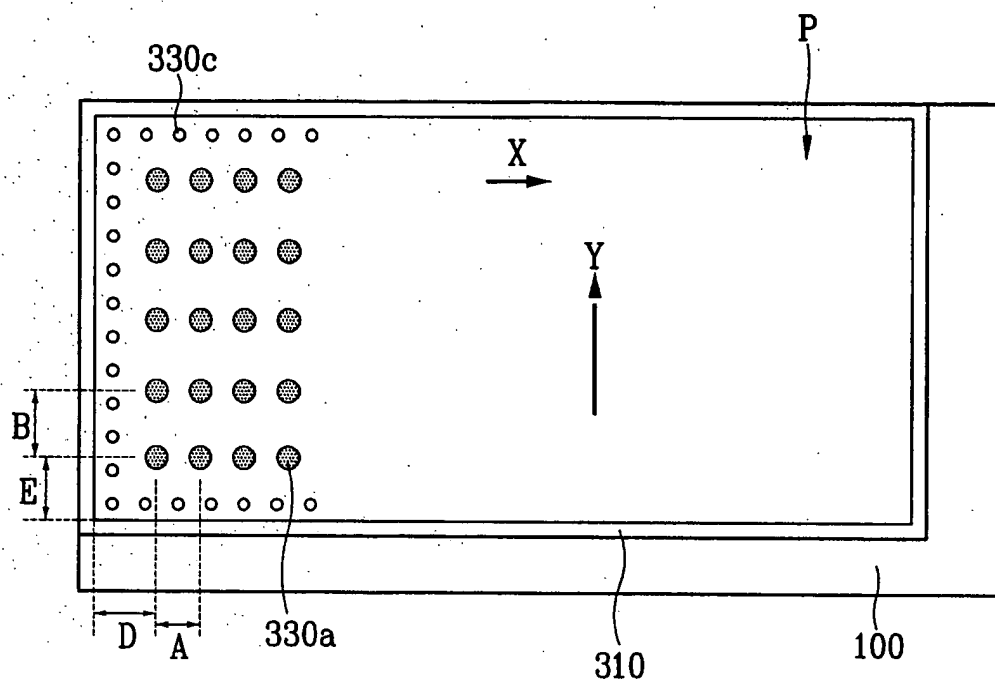


FIG. 9B

